

# CBCS SCHEME

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15EC655

## Sixth Semester B.E. Degree Examination, June/July 2019 Microelectronics

Time: 3 hrs.

Max. Marks: 80

*Note: Answer any FIVE full questions, choosing ONE full question from each module.*

### Module-1

- 1 a. Derive the expression of drain current of a MOS device for triode and saturation region. (08 Marks)
- b. Consider a CMOS process for which  $L_{\min} = 0.4\mu\text{m}$ ,  $t_{\text{ox}} = 8\text{nm}$ ,  $\mu_n = 450\text{cm}^2/\text{v.s}$  and  $v_t = 0.7\text{V}$ 
  - i) Find  $C_{\text{ox}}$  and  $k_n^1$
  - ii) For an NMOS transistor  $\frac{W}{L} = \frac{8\mu\text{m}}{0.8\mu\text{m}}$ . Calculate the values of  $V_{\text{GS}}$  and  $V_{\text{DSmin}}$  needed to operate a transistor in saturation region with a DC current  $I_D = 100\mu\text{A}$ .
  - iii) For the derive in (ii), find the value of  $V_{\text{GS}}$  required to cause the device to operate as  $1000\Omega$  resistor for a very small  $V_{\text{DS}}$ . (08 Marks)

OR

- 2 a. With the neat diagram obtain the expression for finite O/P resistance in saturation region. (07 Marks)
- b. Define the following parameter with respect to MOSFET:
  - i) Threshold voltage
  - ii) Body Effect. (05 Marks)
- c. For the circuit shown in Fig.Q.2(c), find the values of  $R$  and  $V_D$  to obtain a current  $I_D$  of  $80\mu\text{A}$ . Let the NMOS transistor have  $V_t = 0.6\text{V}$ ,  $\mu_n C_{\text{ox}} = 200\mu\text{A}/\text{V}^2$ ,  $L = 0.8\mu\text{m}$  and  $W = 4\mu\text{m}$ . Assume  $\lambda = 0$ . (04 Marks)

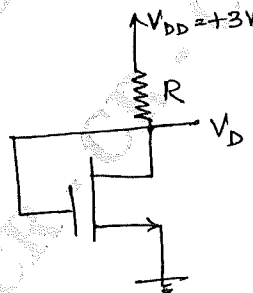


Fig.Q.2(c)

### Module-2

- 3 a. Draw the circuit diagram of source follower amplifier. Draw its small signal equivalent circuit with  $r_o$ . Obtain the expression for  $R_{\text{in}}$ ,  $R_{\text{out}}$ ,  $A_v$ ,  $A_{v_o}$  and  $G_v$ . (10 Marks)
- b. List the various techniques used for biasing in MOS amplifier circuits and explain any two in detail. (06 Marks)

Important Note : 1. On completing your answers, compulsorily draw diagonal cross lines on the remaining blank pages.  
2. Any revealing of identification, appeal to evaluator and /or equations written eg, 42+8=50, will be treated as malpractice.

OR

- 4 a. Draw the development of T-Equivalent circuit model for the MOSFET. (05 Marks)
- b. Explain the high frequency model of MOSFET with a neat diagram and internal capacitances. (06 Marks)
- c. Derive the expression for transconductance  $g_m$  and voltage gain  $A_v$  for a common source amplifier with small input signal. (05 Marks)

**Module-3**

- 5 a. Determine the  $G_v$ ,  $A_v$ ,  $R_{outs}$ ,  $R_{in}$ ,  $A_{v_o}$  for a common source MOS amplifier. (08 Marks)
- b. Derive the expression for determining 3-dB frequency ( $W_H$ ) of an amplifier. (08 Marks)

OR

- 6 a. Explain the operation of a MOSFET current steering circuits with necessary expressions. (08 Marks)
- b. Fig.Q.6(b) shows an ideal voltage amplifier having a gain of  $-100V/V$  with an impedance  $Z$  is
  - i) A  $1M\Omega$  resistance
  - ii) A  $1pF$  capacitance. In each case, use the equivalent circuit to determine  $V_o/V_{sig}$ . (08 Marks)

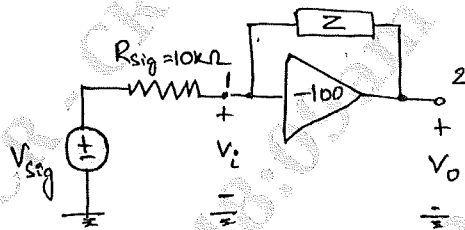


Fig.Q.6(b)

**Module-4**

- 7 a. Consider a CMOS CS amplifier in Fig.Q.7(a) for the case  $V_{DD} = 3V$ ,  $V_{tn} = |V_{tp}| = 0.6V$ ,  $\mu_n C_{ox} = 200\mu A/V^2$ ,  $\mu_p C_{ox} = 65\mu A/V^2$  for all transistors  $L = 0.4\mu m$ ,  $W = 4\mu m$ . Also  $V_{An} = 20V$ ,  $|V_{Ap}| = 10V$ ,  $I_{REF} = 100\mu A$ . Find  $g_{m1}$ ,  $r_{o1}$ ,  $r_{o2}$  and small signal voltage gain. (06 Marks)

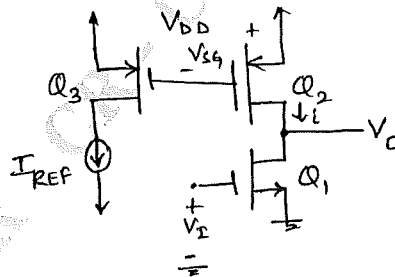


Fig.Q.7(a)

- b. For a common gate amplifier with active load determine the expression for  $R_i$ ,  $A_{v_o}$ ,  $A_v$ ,  $G_{v_o}$ ,  $G_v$ ,  $R_o$ . (10 Marks)

OR

- 8 a. Explain the following: i) Double cascode ii) Folded cascode. (08 Marks)  
 b. Explain the high frequency response of MOS cascode amplifier with necessary diagram and expressions. (08 Marks)

**Module-5**

- 9 a. Explain the operation of MOS differential pair with a differential input voltage. (08 Marks)  
 b. Prove that  $A_{CM} = \frac{-r_{o4}}{2R_{ss}} \times \frac{1}{1 + g_{m3}r_{o3}}$  for the active loaded MOS differential amplifier. (08 Marks)

OR

- 10 a. For the nMOS differential pair with a common mode voltage  $V_{CM}$  applied as shown in Fig.Q.10(a). Let  $V_{DD} = V_{SS} = 2.5V$ ,  $K_n \frac{W}{L} = 3mA/v^2$ ,  $V_{tn} = 0.7V$ ,  $I = 0.2mA$ ,  $R_D = 5K\Omega$ .

Neglect channel length modulation

- i) Find  $V_{OV}$  and  $V_{GS}$  for each transistor  
 ii) For  $V_{CM} = 0$ , Find  $V_S$ ,  $i_{D1}$ ,  $i_{D2}$ ,  $V_{D1}$  and  $V_{D2}$   
 iii) What is highest value of  $V_{cm}$  for which  $Q_1$  and  $Q_2$  remain in saturation, if current source  $I$  requires a minimum voltage of  $0.3V$  to operate properly. What is the lowest value for  $V_s$  and hence for  $V_{cm}$ ?

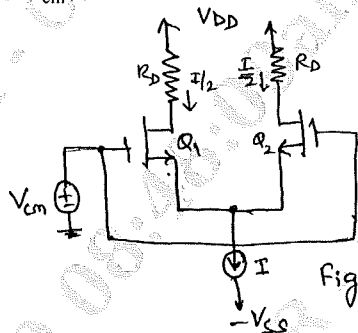


Fig.Q.10(a)

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- b. With neat circuit diagram, explain the operation of two stage CMOS Op-amp configuration. (08 Marks)

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